



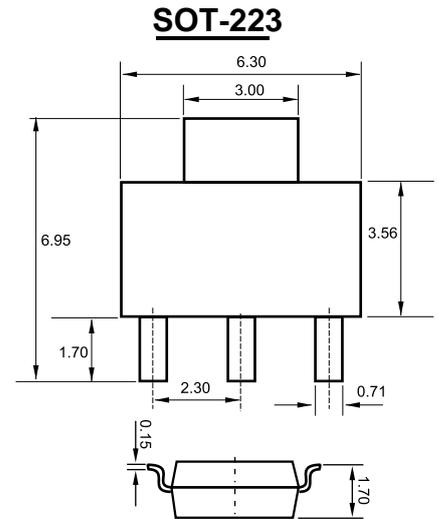
1. BASE
2. COLLECTOR
3. EMITTER

Features

- ✧ High breakdown voltage
- ✧ Low collector-emitter saturation voltage
- ✧ Complementary type: PZTA92(PNP)

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	300	V
V _{CEO}	Collector-Emitter Voltage	300	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current -Continuous	0.5	A
P _C	Collector Power Dissipation	1	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



Dimensions in inches and (millimeters)

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA, I _E =0	300			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	300			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =200V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =6V, I _C =0			0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =10V, I _C =1mA	25			
	h _{FE(2)}	V _{CE} =10V, I _C =10mA	40			
	h _{FE(3)}	V _{CE} =10V, I _C =30mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =20mA, I _B =2mA			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =20mA, I _B =2mA			0.9	V
Transition frequency	f _T	V _{CE} =20V, I _C =10mA, f=100MHz	50			MHz
Collector output capacitance	C _{ob}	V _{CB} =20V, I _E =0, f=1MHz			3	pF

Typical Characteristics

